

Title (en)
CURRENT CONFINEMENT AND BLOCKING REGION FOR SEMICONDUCTOR DEVICES

Publication
EP 0314372 A3 19891025 (EN)

Application
EP 88309770 A 19881019

Priority
US 11491087 A 19871029

Abstract (en)
[origin: EP0314372A2] Improved current confinement and current blocking are achieved in a semiconductor device including a doped (n or p type) semiconductor layer (32) within a region of high resistivity semiconductor material (31,33). In another embodiment, a plurality of doped semiconductor layers are interleaved with a plurality of high resistivity semiconductor layers.

IPC 1-7
H01S 3/19

IPC 8 full level
H01L 33/00 (2010.01); **H01L 33/14** (2010.01); **H01L 33/30** (2010.01); **H01S 5/00** (2006.01); **H01S 5/227** (2006.01); **H01S 5/22** (2006.01)

CPC (source: EP)
H01S 5/227 (2013.01); **H01S 5/2224** (2013.01); **H01S 5/2226** (2013.01); **H01S 5/2227** (2013.01); **H01S 5/2275** (2013.01)

Citation (search report)

- [X] WO 8600172 A1 19860103 - AMERICAN TELEPHONE & TELEGRAPH [US]
- [A] EP 0208209 A2 19870114 - NEC CORP [JP]
- [Y] PATENT ABSTRACTS OF JAPAN

Cited by
US2017373473A1; EP0814549A3; EP1300917A1; EP1372229A1; EP0547850A1; US10374393B2; EP0639875A1; US5838025A; EP2677549A1; FR2992472A1; DE102019134216A1; DE19625599A1; FR2736211A1; US5804840A; FR2727791A1; US5717710A; DE19545164B4; DE19545164B8; US9166091B2; US6937632B2; US6813298B2; WO9502910A1; WO03041121A3; US7208770B2; US7122846B2; US6921925B2; US7087449B2; US6891202B2

Designated contracting state (EPC)
DE FR GB NL SE

DOCDB simple family (publication)
EP 0314372 A2 19890503; EP 0314372 A3 19891025; JP H01146390 A 19890608

DOCDB simple family (application)
EP 88309770 A 19881019; JP 26838788 A 19881026